

## 2SK2957(L), 2SK2957(S)

Silicon N Channel MOS FET  
High Speed Power Switching

REJ03G1057-0600  
(Previous: ADE-208-567D)  
Rev.6.00  
Sep 07, 2005

### Features

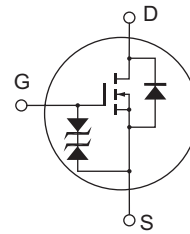
- Low on-resistance  
 $R_{DS(on)} = 7 \text{ m}\Omega$  typ.
- 4 V gate drive devices.
- High speed switching

### Outline

RENESAS Package code: PRSS0004AE-A  
(Package name: LDBPAK(L))



RENESAS Package code: PRSS0004AE-B  
(Package name: LDBPAK(S)-(1))



1. Gate
2. Drain
3. Source
4. Drain

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	30	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	50	A
Drain peak current	I <sub>D(pulse)</sub> <sup>Note1</sup>	200	A
Body-drain diode reverse drain current	I <sub>DR</sub>	50	A
Channel dissipation	P <sub>ch</sub> <sup>Note2</sup>	75	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10μs, duty cycle ≤ 1 %  
 2. Value at Tc = 25°C

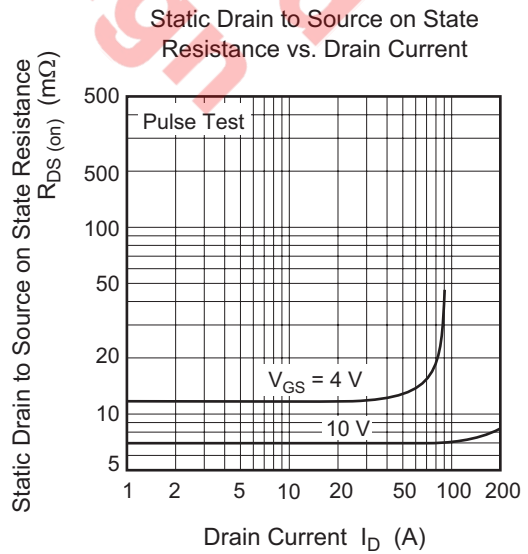
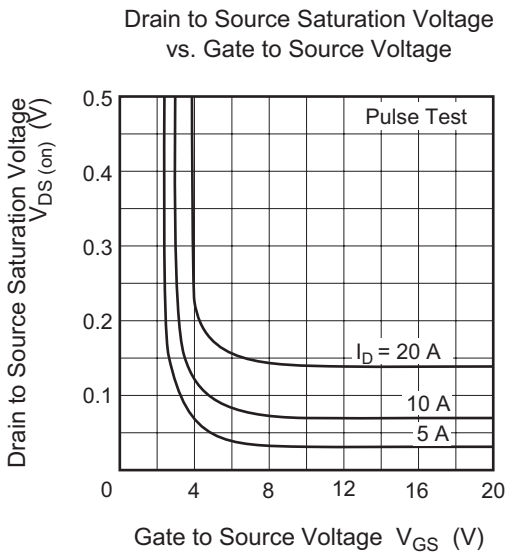
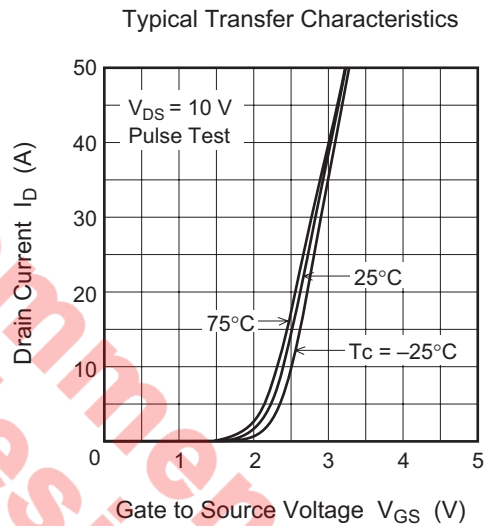
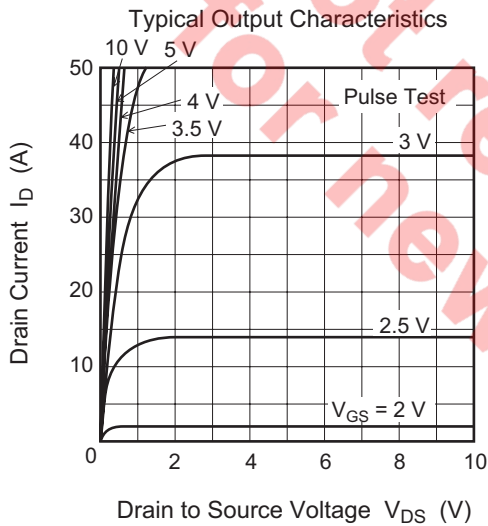
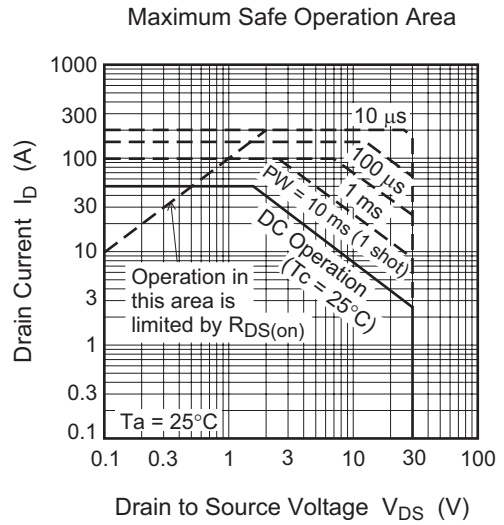
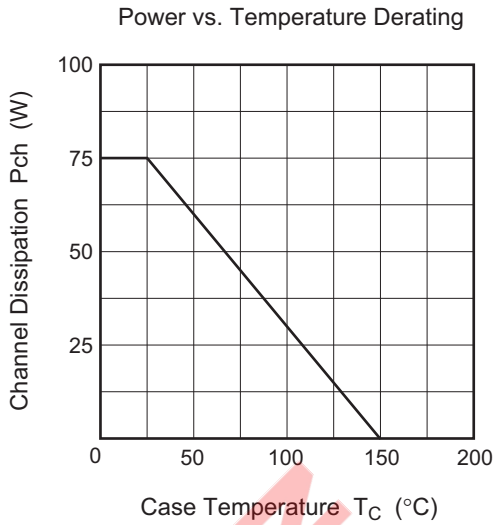
## Electrical Characteristics

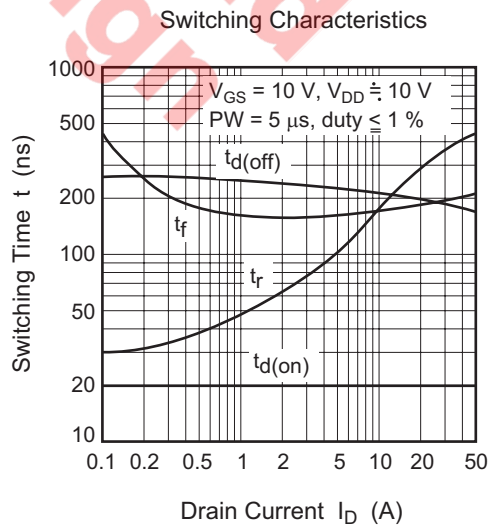
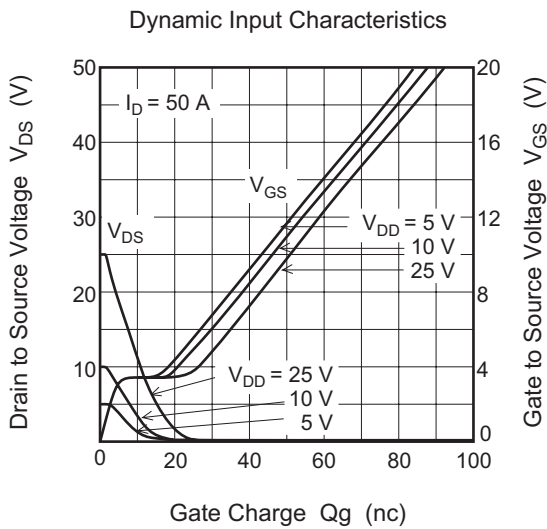
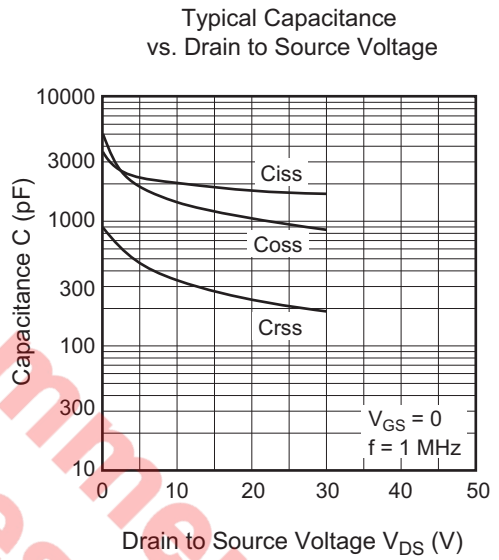
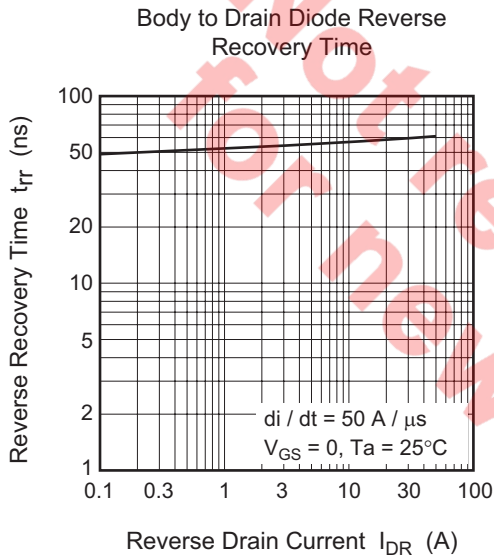
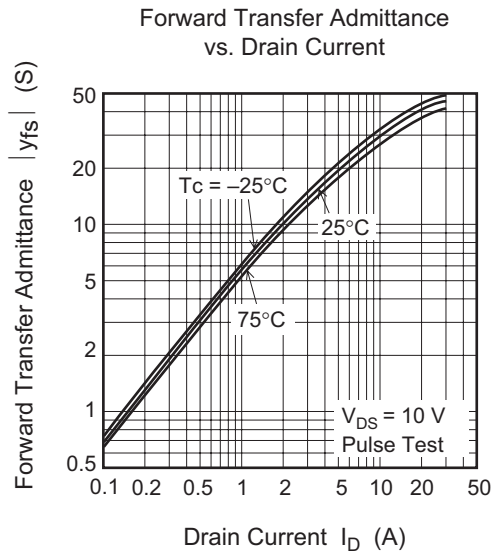
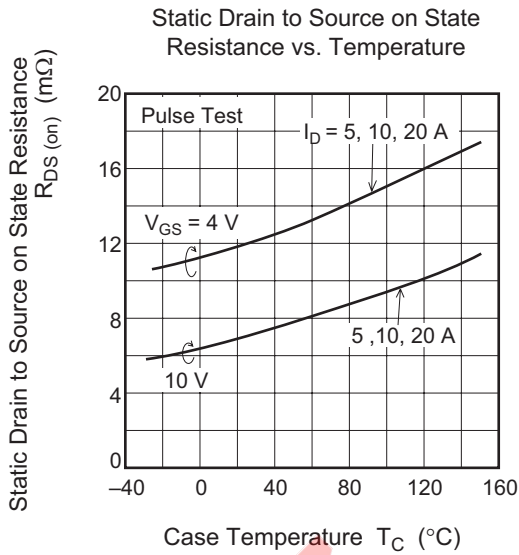
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	30	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±20	—	—	V	I <sub>G</sub> = ±100 μA, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	10	μA	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	1.0	—	2.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Static drain to source on state resistance	R <sub>DS(on)</sub>	—	7.0	10	mΩ	I <sub>D</sub> = 25 A, V <sub>GS</sub> = 10 V <sup>Note3</sup>
	R <sub>DS(on)</sub>	—	12	18	mΩ	I <sub>D</sub> = 25 A, V <sub>GS</sub> = 4 V <sup>Note3</sup>
Forward transfer admittance	y <sub>fs</sub>	25	45	—	S	I <sub>D</sub> = 25 A, V <sub>DS</sub> = 10 V <sup>Note3</sup>
Input capacitance	C <sub>iss</sub>	—	2000	—	pF	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0, f = 1 MHz
Output capacitance	C <sub>oss</sub>	—	1500	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	350	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	20	—	ns	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 25 A, R <sub>L</sub> = 0.4 Ω
Rise time	t <sub>r</sub>	—	330	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	—	190	—	ns	
Fall time	t <sub>f</sub>	—	190	—	ns	
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.95	—	V	I <sub>F</sub> = 50A, V <sub>GS</sub> = 0
Body-drain diode reverse recovery time	t <sub>rr</sub>	—	60	—	ns	I <sub>F</sub> = 50A, V <sub>GS</sub> = 0 di <sub>F</sub> / dt = 50 A/μs

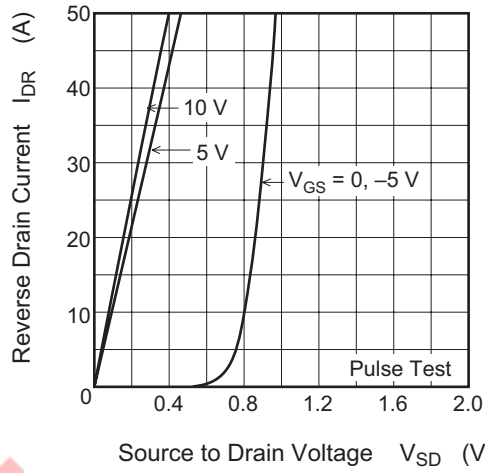
Note: 3. Pulse test

Main Characteristics

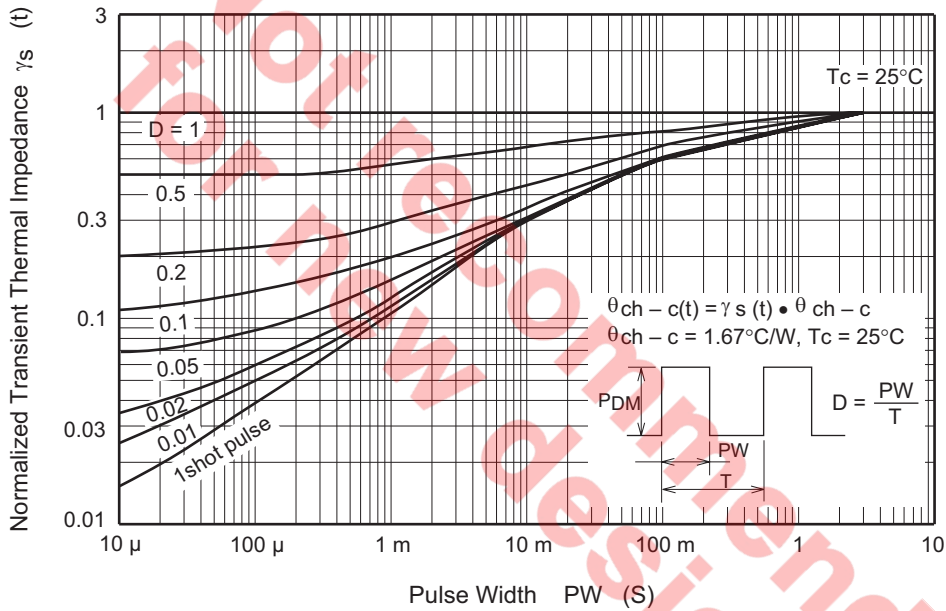




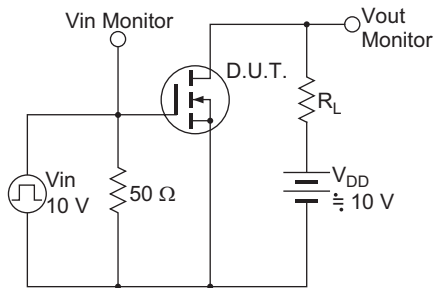
Reverse Drain Current vs. Source to Drain Voltage



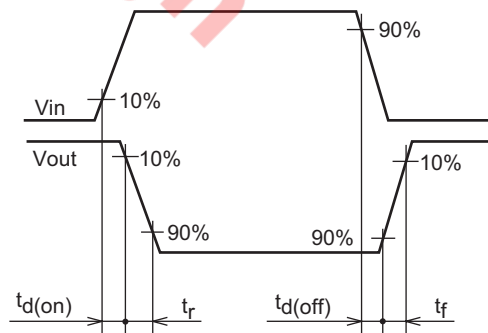
Normalized Transient Thermal Impedance vs. Pulse Width



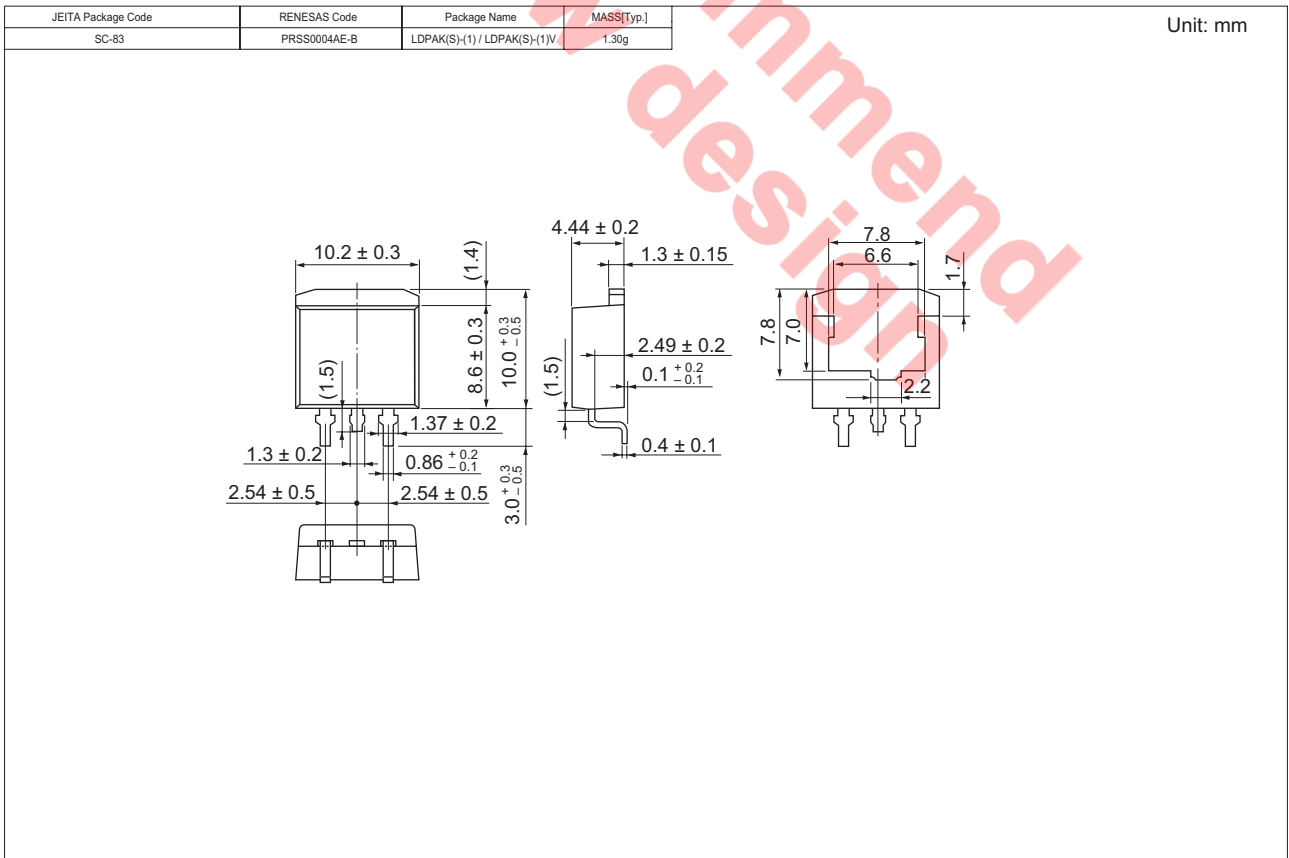
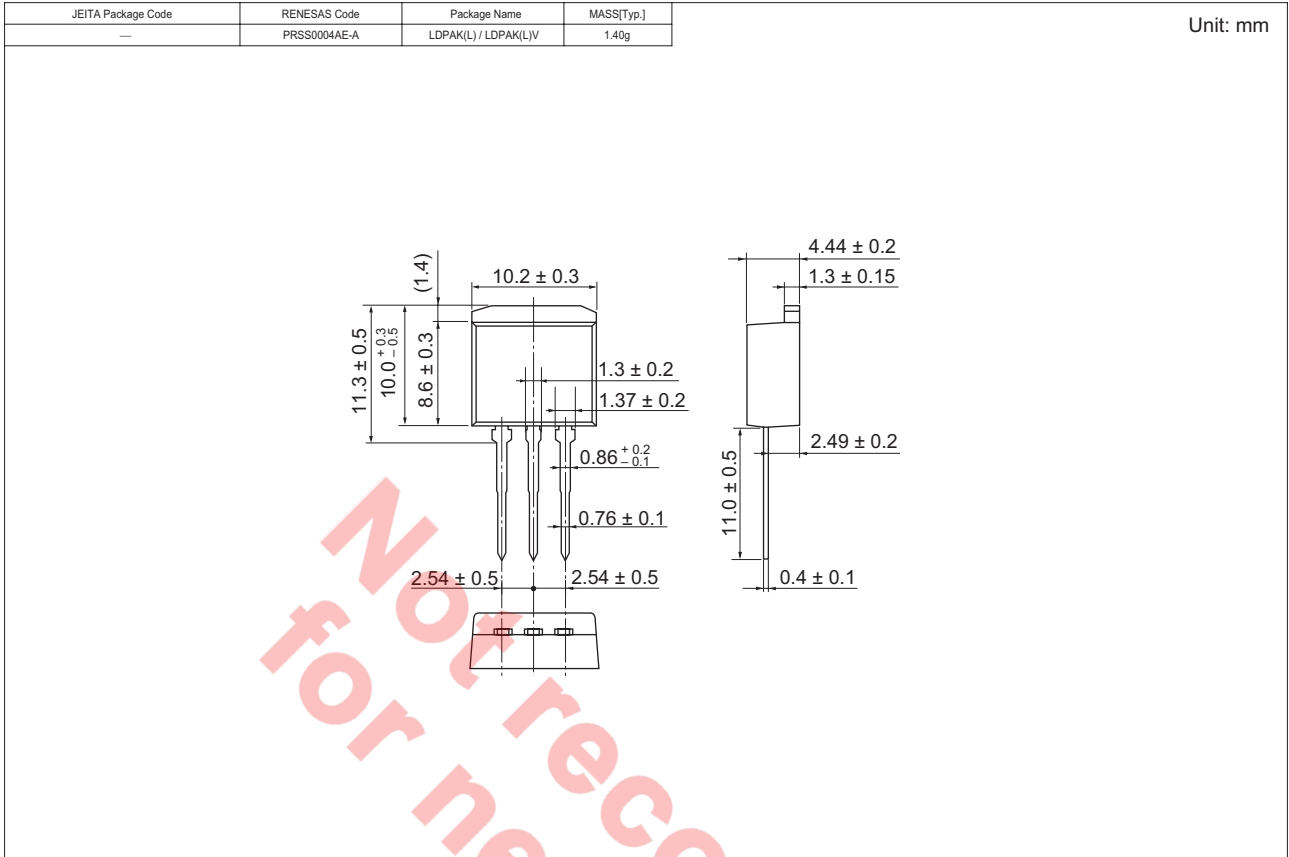
Switching Time Test Circuit



Waveform



Package Dimensions



### Ordering Information

Part Name	Quantity	Shipping Container
2SK2957L-E	500 pcs	Box (Sack)
2SK2957STL-E	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

**Not recommend  
for new design**